





100V PNP LOW SATURATION TRANSISTOR IN SOT23

Features

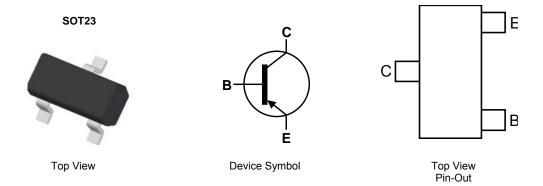
- BV_{CEO} > -100V
- I_C = -1A High Continuous Collector Current
- I_{CM}= -2.5A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -330mV @ -1A
- R_{CE(SAT)} = 210mΩ for a Low Equivalent On-Resistance
- 625mW Power Dissipation
- hFE Characterized up to -1.5A for High Current Gain Hold-Up
- Complementary NPN Type: FMMT624
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.008 grams (Approximate)

Applications

- High-Side Driver
- Load Disconnect Switch
- Motor Drive



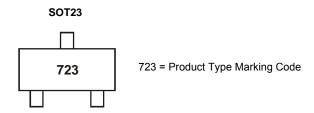
Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FMMT723TA	AEC-Q101	723	7	8	3,000
FMMT723QTA	Automotive	723	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-1	Α
Peak Pulse Current	I _{CM}	-2.5	Α
Base Current	lΒ	-500	mA

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P _D	625	mW
Power Dissipation (Note 7)	P _D	806	mW
Thermal Resistance, Junction to Ambient (Note 6)	R _{0JA}	200	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ heta JA}$	155	°C/W
Thermal Resistance, Junction to Leads (Note 8)	R ₀ JL	194	°C/W
Operating and Storage Temperature Range	$T_{J_i} T_{STG}$	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

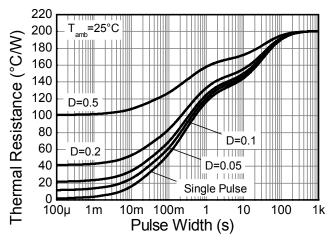
Notes:

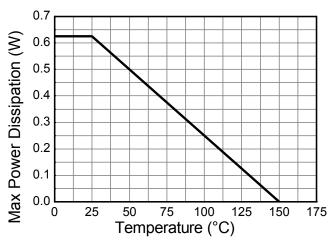
- 6. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as Note 6, except the device is measured at $t \le 5$ sec.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



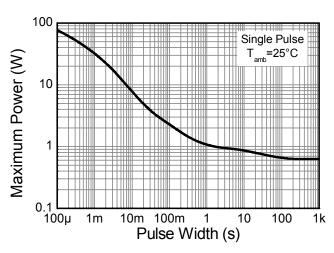


Thermal Characteristics and Derating information

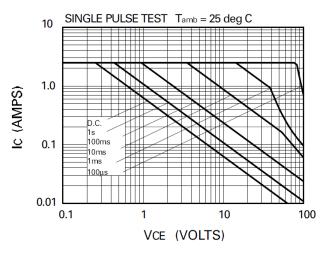




Transient Thermal Impedance



Derating Curve



Pulse Power Dissipation

Safe Operating Area



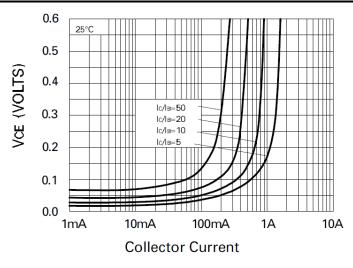
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

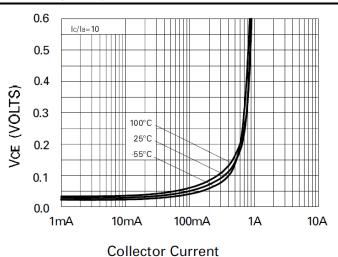
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-100	-200	-	V	$I_{C} = -100\mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV_CEO	-100	-160	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.8	-	V	$I_{E} = -100 \mu A$
Collector Cutoff Current	I _{CBO}	-	<1	-100	nA	V _{CB} = -80V
Emitter Cutoff Current	I _{EBO}	-	<1	-100	nA	V _{EB} = -5.6V
Collector Emitter Cutoff Current	I _{CES}	-	<1	-100	nA	V _{CE} = -80V
		300	475	-		$I_C = -10mA$, $V_{CE} = -10V$
		300	450	-		$I_C = -0.1A$, $V_{CE} = -10V$
Static Forward Current Transfer Ratio (Note 10)	h _{FE}	250	375	-	-	$I_C = -0.5A$, $V_{CE} = -10V$
		-	250	-		I _C = -1A, V _{CE} = -10V
		-	30	-		I _C = -1.5A, V _{CE} = -10V
		-	-50	-80		I _C =- 0.1A, I _B = -10mA
Collector-Emitter Saturation Voltage (Note 10)	$V_{CE(sat)}$	-	-125	-200	mV	$I_C = -0.5A$, $I_B = -50mA$
		-	-210	-330		$I_C = -1A$, $I_B = -150mA$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$	-	-0.71	-1.0	V	$I_C = -1A$, $V_{CE} = -10V$
Base-Emitter Saturation Voltage (Note 10)	V _{BE(sat)}	-	-0.89	-1.0	V	$I_C = -1A$, $I_B = -150mA$
Output Capacitance	C_obo	-	13	20	pF	V _{CB} = -10V, f = 1MHz
Transition Frequency	f _T	150	200	-	MHz	$V_{CE} = -10V$, $I_{C} = -50mA$, $f = 100MHz$
Turn-On Time	t _{on}	-	50	-	ns	$V_{CC} = -50V, I_{C} = -0.5A$
Turn-Off Time	t _{off}	-	760	-	ns	$I_{B1} = I_{B2} = -50 \text{mA}$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

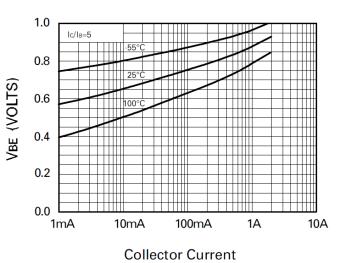




VCE(SAT) vs IC

1.4 100°C 450 VCE=10V 450 VCE=

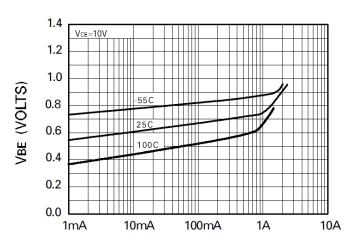
VCE(SAT) vs IC



VBE(SAT) vs IC

Collector Current

hfe vs lc



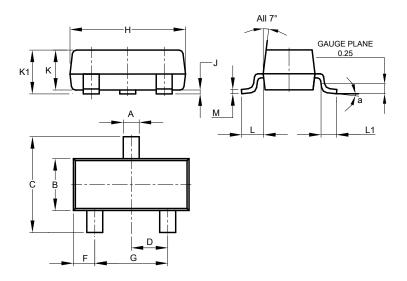
Collector Current

VBE(ON) vs IC



Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

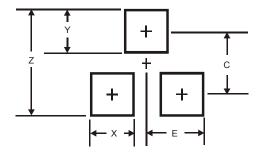


SOT23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
K	0.890	1.00	0.975		
K1	0.903	1.10	1.025		
L	0.45	0.61	0.55		
L1	0.25	0.55	0.40		
М	0.085	0.150	0.110		
а	a 8°				
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.





Dimensions	Value (in mm)		
Z	2.9		
Х	0.8		
Y	0.9		
С	2.0		
Е	1.35		

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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